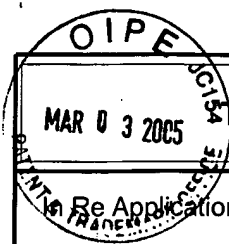


DFW



TRANSMITTAL OF FORMAL DRAWINGS

Docket No.
YOR920030203US1 (16694)

Re Application Of: **Stephen W. Bedell, et al.**

Application No.	Filing Date	Confirmation No.	Examiner	Customer No.	Group Art Unit
10/662,028	September 12, 2003	9297	Unassigned	23389	3661


Invention: **FORMATION OF A SILICON GERMANIUM-ON-INSULATOR STRUCTURE BY OXIDATION OF A BURIED POROUS SILICON LAYER**

Address to:
**Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450**

Transmitted herewith are:

7 sheets of formal drawing(s) for this application.

☒ Each sheet of drawing indicates the identifying indicia suggested in 37 CFR Section 1.84(c).


Signature

**Leslie S. Szivos, Ph.D.
Registration No. 39,394**

Dated: **March 1, 2005**

I certify that this document and attached formal drawings are being deposited on **03/01/05** with the U.S. Postal Service as first class mail under 37 C.F.R. 1.8 and addressed to the Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.


Signature of Person Mailing Correspondence

Leslie S. Szivos, Ph.D.

Typed or Printed Name of Person Mailing Correspondence